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What is "Embedded - Microcontrollers"?

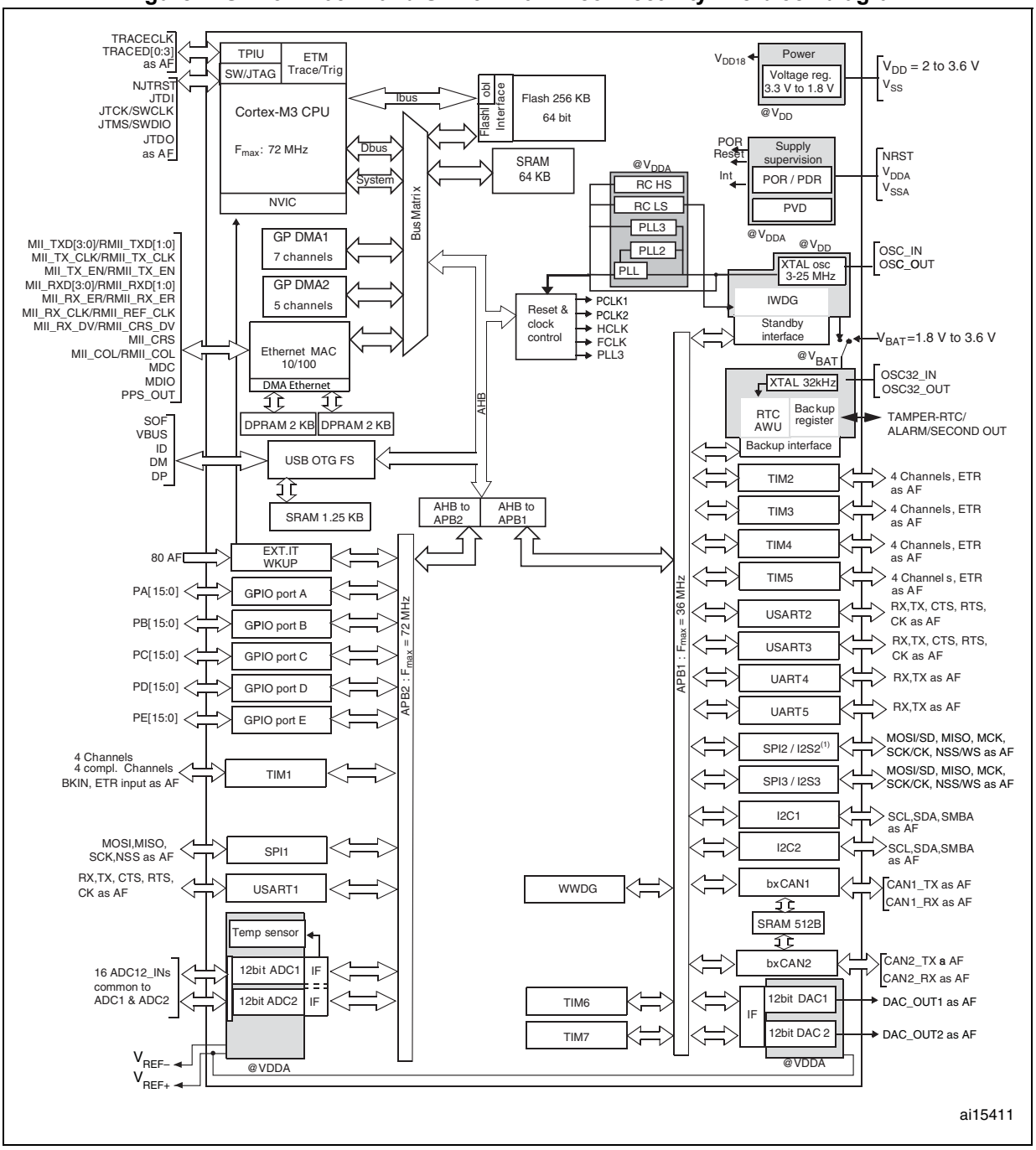
"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	72MHz
Connectivity	CANbus, Ethernet, I²C, IrDA, LINbus, SPI, UART/USART, USB OTG
Peripherals	DMA, POR, PWM, Voltage Detect, WDT
Number of I/O	51
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	64K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f107rbt6

2.3 Overview

Figure 1. STM32F105xx and STM32F107xx connectivity line block diagram



1. T_A = –40 °C to +85 °C (suffix 6, see *Table 62*) or –40 °C to +105 °C (suffix 7, see *Table 62*), junction temperature up to 105 °C or 125 °C, respectively.
2. AF = alternate function on I/O port pin.

2.3.9 Power supply schemes

- V_{DD} = 2.0 to 3.6 V: external power supply for I/Os and the internal regulator. Provided externally through V_{DD} pins.
- V_{SSA}, V_{DDA} = 2.0 to 3.6 V: external analog power supplies for ADC, Reset blocks, RCs and PLL (minimum voltage to be applied to V_{DDA} is 2.4 V when the ADC is used). V_{DDA} and V_{SSA} must be connected to V_{DD} and V_{SS}, respectively.
- V_{BAT} = 1.8 to 3.6 V: power supply for RTC, external clock 32 kHz oscillator and backup registers (through power switch) when V_{DD} is not present.

2.3.10 Power supply supervisor

The device has an integrated power-on reset (POR)/power-down reset (PDR) circuitry. It is always active, and ensures proper operation starting from/down to 2 V. The device remains in reset mode when V_{DD} is below a specified threshold, $V_{POR/PDR}$, without the need for an external reset circuit.

The device features an embedded programmable voltage detector (PVD) that monitors the V_{DD}/V_{DDA} power supply and compares it to the V_{PVD} threshold. An interrupt can be generated when V_{DD}/V_{DDA} drops below the V_{PVD} threshold and/or when V_{DD}/V_{DDA} is higher than the V_{PVD} threshold. The interrupt service routine can then generate a warning message and/or put the MCU into a safe state. The PVD is enabled by software.

2.3.11 Voltage regulator

The regulator has three operation modes: main (MR), low power (LPR) and power down.

- MR is used in the nominal regulation mode (Run)
- LPR is used in the Stop modes.
- Power down is used in Standby mode: the regulator output is in high impedance: the kernel circuitry is powered down, inducing zero consumption (but the contents of the registers and SRAM are lost)

This regulator is always enabled after reset. It is disabled in Standby mode.

2.3.12 Low-power modes

The STM32F105xx and STM32F107xx connectivity line supports three low-power modes to achieve the best compromise between low power consumption, short startup time and available wakeup sources:

- **Sleep** mode

  In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs.

- **Stop** mode

  Stop mode achieves the lowest power consumption while retaining the content of SRAM and registers. All clocks in the 1.8 V domain are stopped, the PLL, the HSI RC and the HSE crystal oscillators are disabled. The voltage regulator can also be put either in normal or in low-power mode.
  The device can be woken up from Stop mode by any of the EXTI line. The EXTI line source can be one of the 16 external lines, the PVD output, the RTC alarm or the USB OTG FS wakeup.

Any of the standard timers can be used to generate PWM outputs. Each of the timers has independent DMA request generations.

Basic timers TIM6 and TIM7

These timers are mainly used for DAC trigger generation. They can also be used as a generic 16-bit time base.

Independent watchdog

The independent watchdog is based on a 12-bit downcounter and 8-bit prescaler. It is clocked from an independent 40 kHz internal RC and as it operates independently from the main clock, it can operate in Stop and Standby modes. It can be used either as a watchdog to reset the device when a problem occurs, or as a free running timer for application timeout management. It is hardware or software configurable through the option bytes. The counter can be frozen in debug mode.

Window watchdog

The window watchdog is based on a 7-bit downcounter that can be set as free running. It can be used as a watchdog to reset the device when a problem occurs. It is clocked from the main clock. It has an early warning interrupt capability and the counter can be frozen in debug mode.

SysTick timer

This timer is dedicated to real-time operating systems, but could also be used as a standard down counter. It features:

- A 24-bit down counter
- Autoreload capability
- Maskable system interrupt generation when the counter reaches 0.
- Programmable clock source

2.3.16 I²C bus

Up to two I²C bus interfaces can operate in multimaster and slave modes. They can support standard and fast modes.

They support 7/10-bit addressing mode and 7-bit dual addressing mode (as slave). A hardware CRC generation/verification is embedded.

They can be served by DMA and they support SMBus 2.0/PMBus.

2.3.17 Universal synchronous/asynchronous receiver transmitters (USARTs)

The STM32F105xx and STM32F107xx connectivity line embeds three universal synchronous/asynchronous receiver transmitters (USART1, USART2 and USART3) and two universal asynchronous receiver transmitters (UART4 and UART5).

These five interfaces provide asynchronous communication, IrDA SIR ENDEC support, multiprocessor communication mode, single-wire half-duplex communication mode and have LIN Master/Slave capability.

The USART1 interface is able to communicate at speeds of up to 4.5 Mbit/s. The other available interfaces communicate at up to 2.25 Mbit/s.

Table 5. Pin definitions (continued)

Pins			Pin name	Type[1]	I / O Level[2]	Main function[3] (after reset)	Alternate functions[4]	
BGA100	LQFP64	LQFP100					Default	Remap
K5	-	40	PE9	I/O	FT	PE9	-	TIM1_CH1
-	-	-	V_{SS_7}	S	-	-	-	-
-	-	-	V_{DD_7}	S	-	-	-	-
G6	-	41	PE10	I/O	FT	PE10	-	TIM1_CH2N
H6	-	42	PE11	I/O	FT	PE11	-	TIM1_CH2
J6	-	43	PE12	I/O	FT	PE12	-	TIM1_CH3N
K6	-	44	PE13	I/O	FT	PE13	-	TIM1_CH3
G7	-	45	PE14	I/O	FT	PE14	-	TIM1_CH4
H7	-	46	PE15	I/O	FT	PE15	-	TIM1_BKIN
J7	29	47	PB10	I/O	FT	PB10	I2C2_SCL[8]/USART3_TX[7]/ ETH_MII_RX_ER	TIM2_CH3
K7	30	48	PB11	I/O	FT	PB11	I2C2_SDA[8]/USART3_RX[7]/ ETH_MII_TX_EN/ ETH_RMII_TX_EN	TIM2_CH4
E7	31	49	V_{SS_1}	S	-	V_{SS_1}	-	-
F7	32	50	V_{DD_1}	S	-	V_{DD_1}	-	-
K8	33	51	PB12	I/O	FT	PB12	SPI2_NSS[8]/I2S2_WS[8]/ I2C2_SMBA[8] / USART3_CK[7]/ TIM1_BKIN[7] / CAN2_RX/ ETH_MII_TXD0/ ETH_RMII_TXD0	-
J8	34	52	PB13	I/O	FT	PB13	SPI2_SCK[8] / I2S2_CK[8] / USART3_CTS[7]/ TIM1_CH1N/CAN2_TX/ ETH_MII_TXD1/ ETH_RMII_TXD1	-
H8	35	53	PB14	I/O	FT	PB14	SPI2_MISO[8] / TIM1_CH2N / USART3_RTS[7]	-
G8	36	54	PB15	I/O	FT	PB15	SPI2_MOSI[8] / I2S2_SD[8] / TIM1_CH3N[7]	-
K9	-	55	PD8	I/O	FT	PD8	-	USART3_TX/ ETH_MII_RX_DV/ ETH_RMII_CRS_DV

Table 5. Pin definitions (continued)

Pins			Pin name	Type[1]	I / O Level[2]	Main function[3] (after reset)	Alternate functions[4]	
BGA100	LQFP64	LQFP100					Default	Remap
J9	-	56	PD9	I/O	FT	PD9	-	USART3_RX/ ETH_MII_RXD0/ ETH_RMII_RXD0
H9	-	57	PD10	I/O	FT	PD10	-	USART3_CK/ ETH_MII_RXD1/ ETH_RMII_RXD1
G9	-	58	PD11	I/O	FT	PD11	-	USART3_CTS/ ETH_MII_RXD2
K10	-	59	PD12	I/O	FT	PD12	-	TIM4_CH1 / USART3_RTS/ ETH_MII_RXD3
J10	-	60	PD13	I/O	FT	PD13	-	TIM4_CH2
H10	-	61	PD14	I/O	FT	PD14	-	TIM4_CH3
G10	-	62	PD15	I/O	FT	PD15	-	TIM4_CH4
F10	37	63	PC6	I/O	FT	PC6	I2S2_MCK/	TIM3_CH1
E10	38	64	PC7	I/O	FT	PC7	I2S3_MCK	TIM3_CH2
F9	39	65	PC8	I/O	FT	PC8	-	TIM3_CH3
E9	40	66	PC9	I/O	FT	PC9	-	TIM3_CH4
D9	41	67	PA8	I/O	FT	PA8	USART1_CK/OTG_FS_SOF / TIM1_CH1[8]/MCO	-
C9	42	68	PA9	I/O	FT	PA9	USART1_TX[7]/ TIM1_CH2[7]/ OTG_FS_VBUS	-
D10	43	69	PA10	I/O	FT	PA10	USART1_RX[7]/ TIM1_CH3[7]/OTG_FS_ID	-
C10	44	70	PA11	I/O	FT	PA11	USART1_CTS / CAN1_RX / TIM1_CH4[7]/OTG_FS_DM	-
B10	45	71	PA12	I/O	FT	PA12	USART1_RTS / OTG_FS_DP / CAN1_TX[7] / TIM1_ETR[7]	-
A10	46	72	PA13	I/O	FT	JTMS-SWDIO	-	PA13
F8	-	73	Not connected					-
E6	47	74	V_{SS_2}	S	-	V_{SS_2}	-	-
F6	48	75	V_{DD_2}	S	-	V_{DD_2}	-	-
A9	49	76	PA14	I/O	FT	JTCK-SWCLK	-	PA14

Table 5. Pin definitions (continued)

Pins			Pin name	Type[1]	I / O Level[2]	Main function[3] (after reset)	Alternate functions[4]	
BGA100	LQFP64	LQFP100					Default	Remap
A8	50	77	PA15	I/O	FT	JTDI	SPI3_NSS / I2S3_WS	TIM2_CH1_ETR / PA15 SPI1_NSS
B9	51	78	PC10	I/O	FT	PC10	UART4_TX	USART3_TX/ SPI3_SCK/I2S3_CK
B8	52	79	PC11	I/O	FT	PC11	UART4_RX	USART3_RX/ SPI3_MISO
C8	53	80	PC12	I/O	FT	PC12	UART5_TX	USART3_CK/ SPI3_MOSI/I2S3_SD
D8	-	81	PD0	I/O	FT	PD0	-	OSC_IN[9]/CAN1_RX
E8	-	82	PD1	I/O	FT	PD1	-	OSC_OUT[9]/CAN1_TX
B7	54	83	PD2	I/O	FT	PD2	TIM3_ETR / UART5_RX	
C7	-	84	PD3	I/O	FT	PD3	-	USART2_CTS
D7	-	85	PD4	I/O	FT	PD4	-	USART2_RTS
B6	-	86	PD5	I/O	FT	PD5	-	USART2_TX
C6	-	87	PD6	I/O	FT	PD6	-	USART2_RX
D6	-	88	PD7	I/O	FT	PD7	-	USART2_CK
A7	55	89	PB3	I/O	FT	JTDO	SPI3_SCK / I2S3_CK	PB3 / TRACESWO/ TIM2_CH2 / SPI1_SCK
A6	56	90	PB4	I/O	FT	NJTRST	SPI3_MISO	PB4 / TIM3_CH1/ SPI1_MISO
C5	57	91	PB5	I/O	-	PB5	I2C1_SMBA / SPI3_MOSI / ETH_MII_PPS_OUT / I2S3_SD ETH_RMII_PPS_OUT	TIM3_CH2/SPI1_MOSI/ CAN2_RX
B5	58	92	PB6	I/O	FT	PB6	I2C1_SCL[7]/TIM4_CH1[7]	USART1_TX/CAN2_TX
A5	59	93	PB7	I/O	FT	PB7	I2C1_SDA[7]/TIM4_CH2[7]	USART1_RX
D5	60	94	BOOT0	I	-	BOOT0	-	-
B4	61	95	PB8	I/O	FT	PB8	TIM4_CH3[7]/ ETH_MII_TXD3	I2C1_SCL/CAN1_RX
A4	62	96	PB9	I/O	FT	PB9	TIM4_CH4[7]	I2C1_SDA / CAN1_TX
D4	-	97	PE0	I/O	FT	PE0	TIM4_ETR	-
C4	-	98	PE1	I/O	FT	PE1	-	-
E5	63	99	V_{SS_3}	S	-	V_{SS_3}	-	-
F5	64	100	V_{DD_3}	S	-	V_{DD_3}	-	-

5 Electrical characteristics

5.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to V_{SS}.

5.1.1 Minimum and maximum values

Unless otherwise specified the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at T_A = 25 °C and T_A = $T_A$max (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation (mean±3Σ).

5.1.2 Typical values

Unless otherwise specified, typical data are based on T_A = 25 °C, V_{DD} = 3.3 V (for the 2 V ≤V_{DD} ≤3.6 V voltage range). They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated (mean±2Σ).

5.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

5.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in *Figure 6*.

5.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in *Figure 7*.

Figure 6. Pin loading conditions

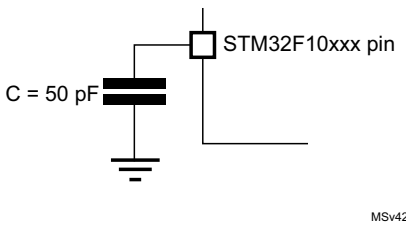
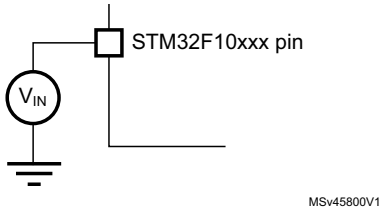


Figure 7. Pin input voltage



5.3.4 Embedded reference voltage

The parameters given in *Table 12* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 9*.

Table 12. Embedded internal reference voltage

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{REFINT}	Internal reference voltage	–40 °C < T_A < +105 °C	1.16	1.20	1.26	V
		–40 °C < T_A < +85 °C	1.16	1.20	1.24	V
$T_{S\_vrefint}$(1)	ADC sampling time when reading the internal reference voltage	-	-	5.1	17.1(2)	µs
V_{RERINT}(2)	Internal reference voltage spread over the temperature range	V_{DD} = 3 V ±10 mV	-	-	10	mV
T_{Coeff}(2)	Temperature coefficient	-	-	-	100	ppm/°C

1. Shortest sampling time can be determined in the application by multiple iterations.
2. Guaranteed by design, not tested in production.

5.3.5 Supply current characteristics

The current consumption is a function of several parameters and factors such as the operating voltage, ambient temperature, I/O pin loading, device software configuration, operating frequencies, I/O pin switching rate, program location in memory and executed binary code.
The current consumption is measured as described in *Figure 9: Current consumption measurement scheme*.
All Run-mode current consumption measurements given in this section are performed with a reduced code that gives a consumption equivalent to Dhrystone 2.1 code.

Maximum current consumption

The MCU is placed under the following conditions:

- All I/O pins are in input mode with a static value at V_{DD} or V_{SS} (no load)
- All peripherals are disabled except when explicitly mentioned
- The Flash memory access time is adjusted to the f_{HCLK} frequency (0 wait state from 0 to 24 MHz, 1 wait state from 24 to 48 MHz and 2 wait states above)
- Prefetch in ON (reminder: this bit must be set before clock setting and bus prescaling)
- When the peripherals are enabled $f_{PCLK1} = f_{HCLK}/2$, $f_{PCLK2} = f_{HCLK}$

The parameters given in *Table 13*, *Table 14* and *Table 15* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 9*.

Table 19. Peripheral current consumption (continued)

Peripheral		Typical consumption at 25 °C	Unit
APB2 (up to 72 MHz)	APB2-Bridge	3.47	µA/MHz
	GPIOA	6.39	
	GPIOB	6.39	
	GPIOC	6.11	
	GPIOD	6.39	
	GPIOE	6.11	
	SPI1	3.61	
	USART1	12.08	
	TIM1	23.47	
	ADC1(4)	18.21	

1. The BusMatrix is automatically active when at least one master is ON.(CPU, ETH-MAC, DMA1 or DMA2).
2. When I2S is enabled we have a consumption add equal to 0, 02 mA.
3. When DAC_OUT1 or DAC_OUT2 is enabled we have a consumption add equal to 0, 3 mA.
4. Specific conditions for measuring ADC current consumption: f_{HCLK} = 56 MHz, $f_{APB1} = f_{HCLK}/2$, $f_{APB2} = f_{HCLK}$, $f_{ADCCLK} = f_{APB2}/4$. When ADON bit in the ADC_CR2 register is set to 1, a current consumption of analog part equal to 0.6 mA must be added.

5.3.6 External clock source characteristics

High-speed external user clock generated from an external source

The characteristics given in *Table 20* result from tests performed using an high-speed external clock source, and under ambient temperature and supply voltage conditions summarized in *Table 9*.

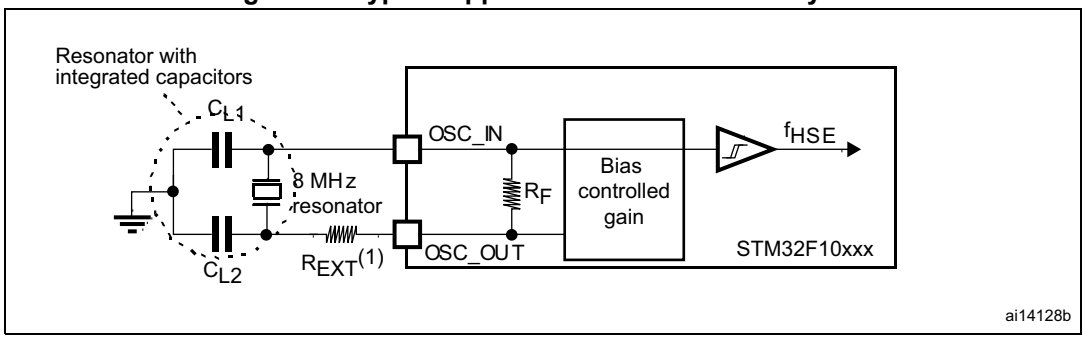
Table 20. High-speed external user clock characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSE_ext}	External user clock source frequency(1)	-	1	8	50	MHz
V_{HSEH}	OSC_IN input pin high level voltage		$0.7V_{DD}$	-	V_{DD}	V
V_{HSEL}	OSC_IN input pin low level voltage		V_{SS}	-	$0.3V_{DD}$	
$t_{w(HSE)}$ $t_{w(HSE)}$	OSC_IN high or low time(1)		5	-	-	ns
$t_{r(HSE)}$ $t_{f(HSE)}$	OSC_IN rise or fall time(1)		-	-	20	
$C_{in(HSE)}$	OSC_IN input capacitance(1)	-	-	5	-	pF
$DuCy_{(HSE)}$	Duty cycle	-	45	-	55	%
I_L	OSC_IN Input leakage current	$V_{SS} \leq V_{IN} \leq V_{DD}$	-	-	±1	µA

1. Guaranteed by design, not tested in production.

For C_{L1} and C_{L2}, it is recommended to use high-quality external ceramic capacitors in the 5 pF to 25 pF range (typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator (see *Figure 16*). C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2}. PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing C_{L1} and C_{L2}. Refer to the application note AN2867 “Oscillator design guide for ST microcontrollers” available from the ST website *www.st.com*.

Figure 16. Typical application with an 8 MHz crystal



1. R_{EXT} value depends on the crystal characteristics.

Low-speed external clock generated from a crystal/ceramic resonator

The low-speed external (LSE) clock can be supplied with a 32.768 kHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in *Table 23*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Table 23. LSE oscillator characteristics (f_{LSE} = 32.768 kHz) (1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
R_F	Feedback resistor	-	-	5	-	MΩ
$C^{(2)}$	Recommended load capacitance versus equivalent serial resistance of the crystal (R_S)(3)	R_S = 30 kΩ	-	-	15	pF
I_2	LSE driving current	V_{DD} = 3.3 V, V_{IN} = V_{SS}	-	-	1.4	µA
g_m	Oscillator Transconductance	-	5	-	-	µA/V

operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

Functional susceptibility to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error above a certain limit (>5 LSB TUE), out of spec current injection on adjacent pins or other functional failure (for example reset, oscillator frequency deviation).

The test results are given in *Table 35*

Table 35. I/O current injection susceptibility

Symbol	Description	Functional susceptibility		Unit
		Negative injection	Positive injection	
I_{INJ}	Injected current on OSC_IN32, OSC_OUT32, PA4, PA5, PC13	-0	+0	mA
	Injected current on all FT pins	-5	+0	
	Injected current on any other pin	-5	+5	

5.3.13 I/O port characteristics

General input/output characteristics

Unless otherwise specified, the parameters given in *Table 36* are derived from tests performed under the conditions summarized in *Table 9*. All I/Os are CMOS and TTL compliant.

Table 36. I/O static characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IL}	Standard IO input low level voltage	-	–0.3	-	0.28*(V_{DD}-2 V)+0.8 V	V
	IO FT(1) input low level voltage	-	–0.3	-	0.32*(V_{DD}-2V)+0.75 V	V
V_{IH}	Standard IO input high level voltage	-	0.41*(V_{DD}-2 V)+1.3 V	-	V_{DD}+0.3	V
	IO FT(1) input high level voltage	V_{DD} > 2 V	0.42*(V_{DD}-2 V)+1 V	-	5.5	V
		$V_{DD} \leq$ 2 V			5.2	
V_{hys}	Standard IO Schmitt trigger voltage hysteresis(2)	-	200	-	-	mV
	IO FT Schmitt trigger voltage hysteresis(2)	-	5% V_{DD}(3)	-	-	mV

Figure 19. Standard I/O input characteristics - TTL port

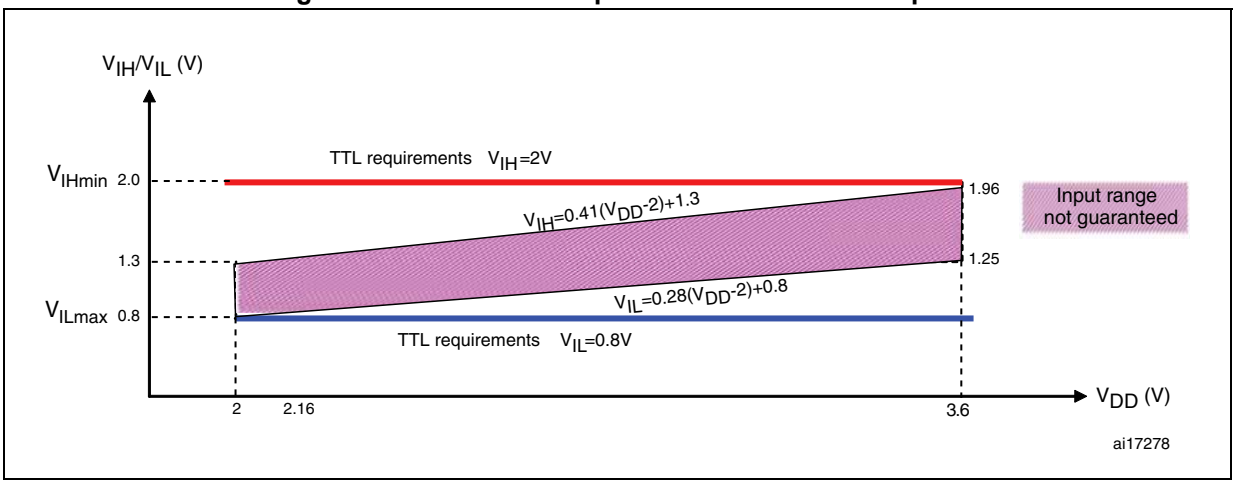


Figure 20. 5 V tolerant I/O input characteristics - CMOS port

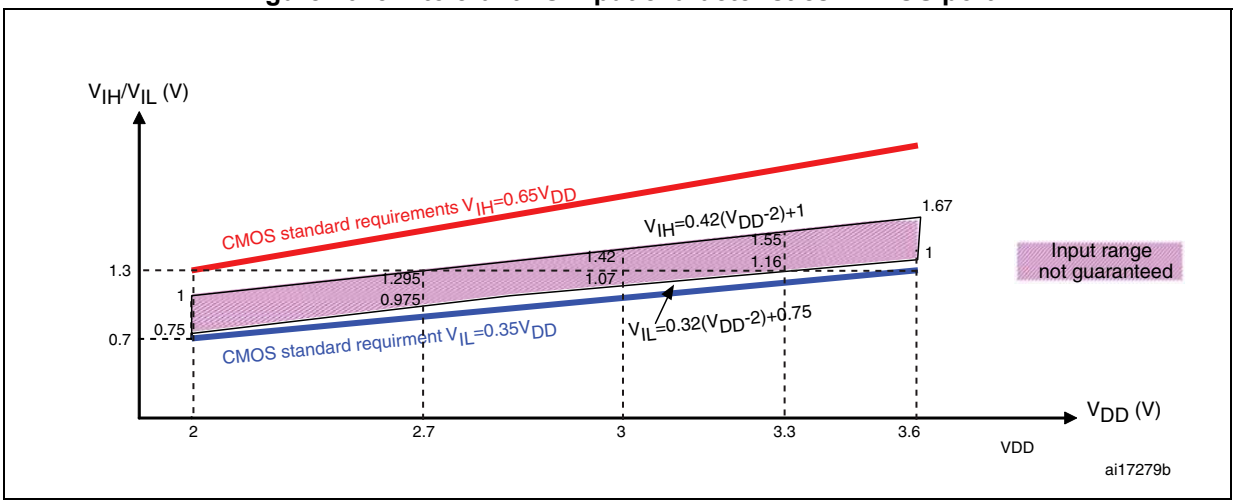
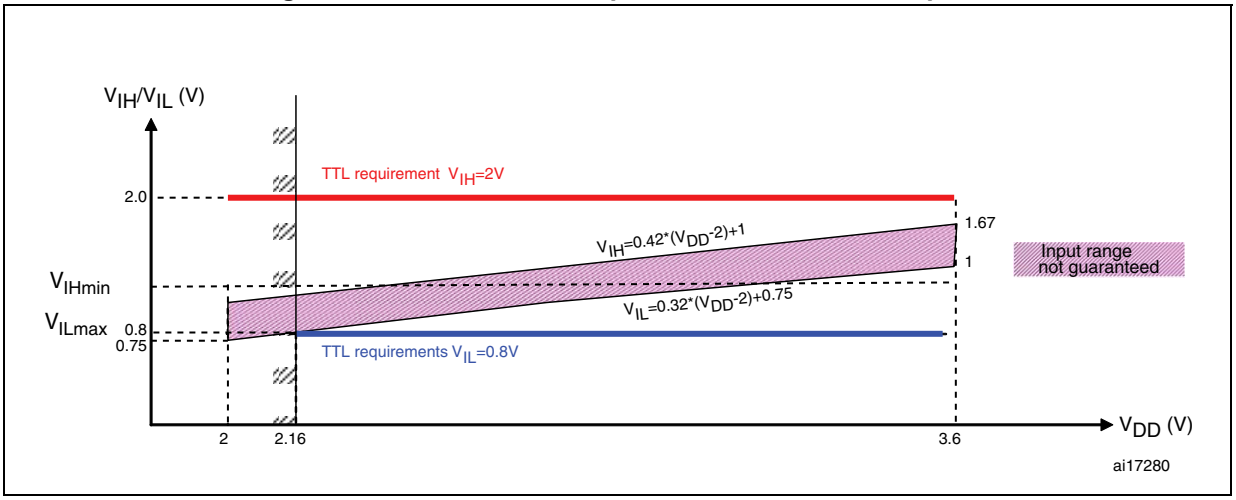


Figure 21. 5 V tolerant I/O input characteristics - TTL port



Output driving current

The GPIOs (general purpose input/outputs) can sink or source up to +/-8 mA, and sink or source up to +/-20 mA (with a relaxed V_{OL}/V_{OH}).

In the user application, the number of I/O pins which can drive current must be limited to respect the absolute maximum rating specified in *Section 5.2*:

- The sum of the currents sourced by all the I/Os on $V_{DD,}$ plus the maximum Run consumption of the MCU sourced on $V_{DD,}$ cannot exceed the absolute maximum rating I_{VDD} (see *Table 7*).
- The sum of the currents sunk by all the I/Os on V_{SS} plus the maximum Run consumption of the MCU sunk on V_{SS} cannot exceed the absolute maximum rating I_{VSS} (see *Table 7*).

Output voltage levels

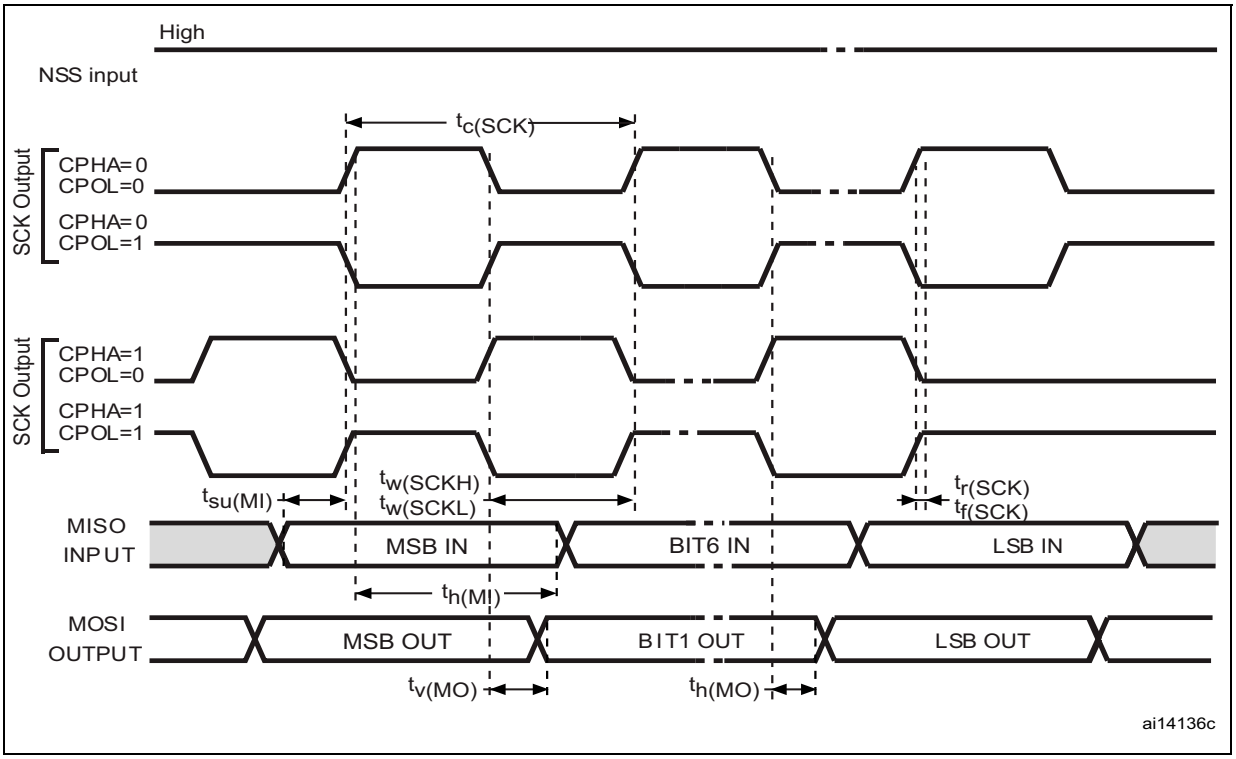
Unless otherwise specified, the parameters given in *Table 37* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 9*. All I/Os are CMOS and TTL compliant.

Table 37. Output voltage characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
V_{OL}(1)	Output low level voltage for an I/O pin when 8 pins are sunk at same time	TTL port I_{IO} = +8 mA 2.7 V < V_{DD} < 3.6 V	-	0.4	V
V_{OH}(2)	Output high level voltage for an I/O pin when 8 pins are sourced at same time		V_{DD}–0.4	-	
V_{OL} (1)	Output low level voltage for an I/O pin when 8 pins are sunk at same time	CMOS port I_{IO} =+ 8mA 2.7 V < V_{DD} < 3.6 V	-	0.4	V
V_{OH} (2)	Output high level voltage for an I/O pin when 8 pins are sourced at same time		2.4	-	
V_{OL}(1)(3)	Output low level voltage for an I/O pin when 8 pins are sunk at same time	I_{IO} = +20 mA 2.7 V < V_{DD} < 3.6 V	-	1.3	V
V_{OH}(2)(3)	Output high level voltage for an I/O pin when 8 pins are sourced at same time		V_{DD}–1.3	-	
V_{OL}(1)(3)	Output low level voltage for an I/O pin when 8 pins are sunk at same time	I_{IO} = +6 mA 2 V < V_{DD} < 2.7 V	-	0.4	V
V_{OH}(2)(3)	Output high level voltage for an I/O pin when 8 pins are sourced at same time		V_{DD}–0.4	-	

1. The I_{IO} current sunk by the device must always respect the absolute maximum rating specified in *Table 7* and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VSS}.
2. The I_{IO} current sourced by the device must always respect the absolute maximum rating specified in *Table 7* and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VDD}.
3. Based on characterization data, not tested in production.

Figure 27. SPI timing diagram - master mode(1)



1. Measurement points are done at CMOS levels: $0.3V_{DD}$ and $0.7V_{DD}$.

5.3.19 Temperature sensor characteristics

Table 57. TS characteristics

Symbol	Parameter	Min	Typ	Max	Unit
T_L (1)	V_{SENSE} linearity with temperature	-	±1	±2	°C
Avg_Slope(1)	Average slope	4.0	4.3	4.6	mV/°C
V_{25} (1)	Voltage at 25 °C	1.34	1.43	1.52	V
t_{START} (2)	Startup time	4	-	10	µs
T_{S_temp} (3)(2)	ADC sampling time when reading the temperature	-	-	17.1	µs

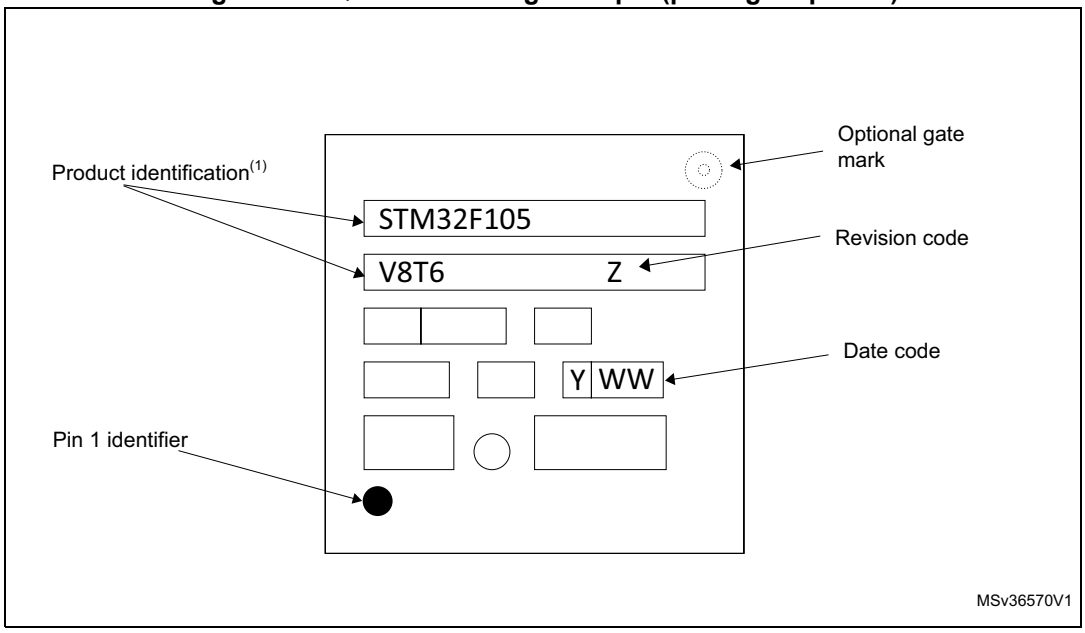
1. Based on characterization, not tested in production.
2. Guaranteed by design, not tested in production.
3. Shortest sampling time can be determined in the application by multiple iterations.

Device marking for LQFP100

The following figure shows the device marking for the LQFP100 package.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 45.LQFP100 marking example (package top view)



1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

6.4.2 Selecting the product temperature range

When ordering the microcontroller, the temperature range is specified in the ordering information scheme shown in *Table 62: Ordering information scheme*.

Each temperature range suffix corresponds to a specific guaranteed ambient temperature at maximum dissipation and, to a specific maximum junction temperature.

As applications do not commonly use the STM32F103xx at maximum dissipation, it is useful to calculate the exact power consumption and junction temperature to determine which temperature range will be best suited to the application.

The following examples show how to calculate the temperature range needed for a given application.

Example 1: High-performance application

Assuming the following application conditions:

Maximum ambient temperature T_{Amax} = 82 °C (measured according to JESD51-2), I_{DDmax} = 50 mA, V_{DD} = 3.5 V, maximum 20 I/Os used at the same time in output at low level with I_{OL} = 8 mA, V_{OL}= 0.4 V and maximum 8 I/Os used at the same time in output at low level with I_{OL} = 20 mA, V_{OL}= 1.3 V

P_{INTmax} = 50 mA × 3.5 V= 175 mW

P_{IOmax} = 20 × 8 mA × 0.4 V + 8 × 20 mA × 1.3 V = 272 mW

This gives: P_{INTmax} = 175 mW and P_{IOmax} = 272 mW:

P_{Dmax} = 175 + 272 = 447 mW

Thus: P_{Dmax} = 447 mW

Using the values obtained in *Table 61* T_{Jmax} is calculated as follows:

– For LQFP100, 46 °C/W

T_{Jmax} = 82 °C + (46 °C/W × 447 mW) = 82 °C + 20.6 °C = 102.6 °C

This is within the range of the suffix 6 version parts (–40 < T_J < 105 °C).

In this case, parts must be ordered at least with the temperature range suffix 6 (see *Table 62: Ordering information scheme*).

Example 2: High-temperature application

Using the same rules, it is possible to address applications that run at high ambient temperatures with a low dissipation, as long as junction temperature T_J remains within the specified range.

Assuming the following application conditions:

Maximum ambient temperature T_{Amax} = 115 °C (measured according to JESD51-2), I_{DDmax} = 20 mA, V_{DD} = 3.5 V, maximum 20 I/Os used at the same time in output at low level with I_{OL} = 8 mA, V_{OL}= 0.4 V

P_{INTmax} = 20 mA × 3.5 V= 70 mW

P_{IOmax} = 20 × 8 mA × 0.4 V = 64 mW

This gives: P_{INTmax} = 70 mW and P_{IOmax} = 64 mW:

P_{Dmax} = 70 + 64 = 134 mW

Thus: P_{Dmax} = 134 mW

Using the values obtained in *Table 61* T_{Jmax} is calculated as follows:

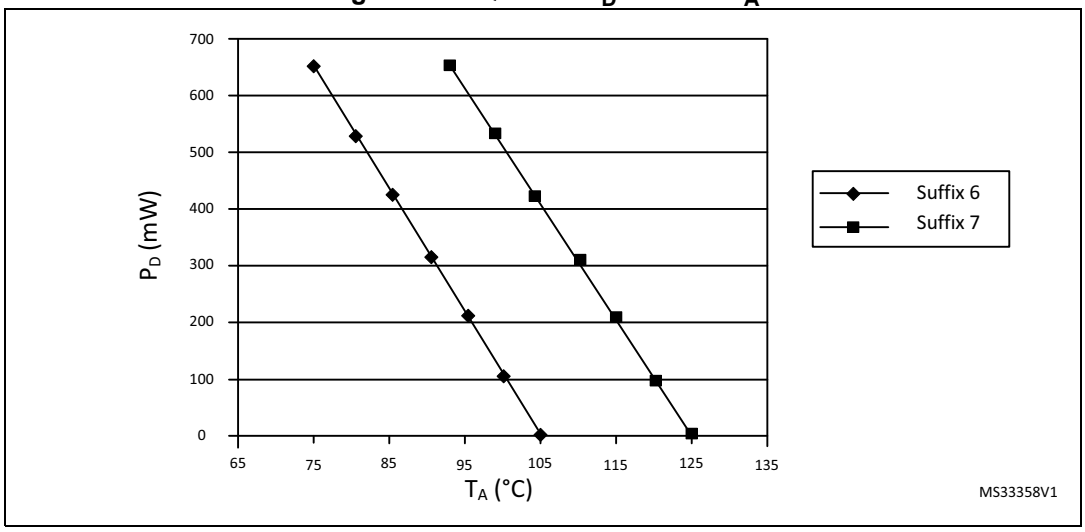
– For LQFP100, 46 °C/W

T_{Jmax} = 115 °C + (46 °C/W × 134 mW) = 115 °C + 6.2 °C = 121.2 °C

This is within the range of the suffix 7 version parts (–40 < T_J < 125 °C).

In this case, parts must be ordered at least with the temperature range suffix 7 (see *Table 62: Ordering information scheme*).

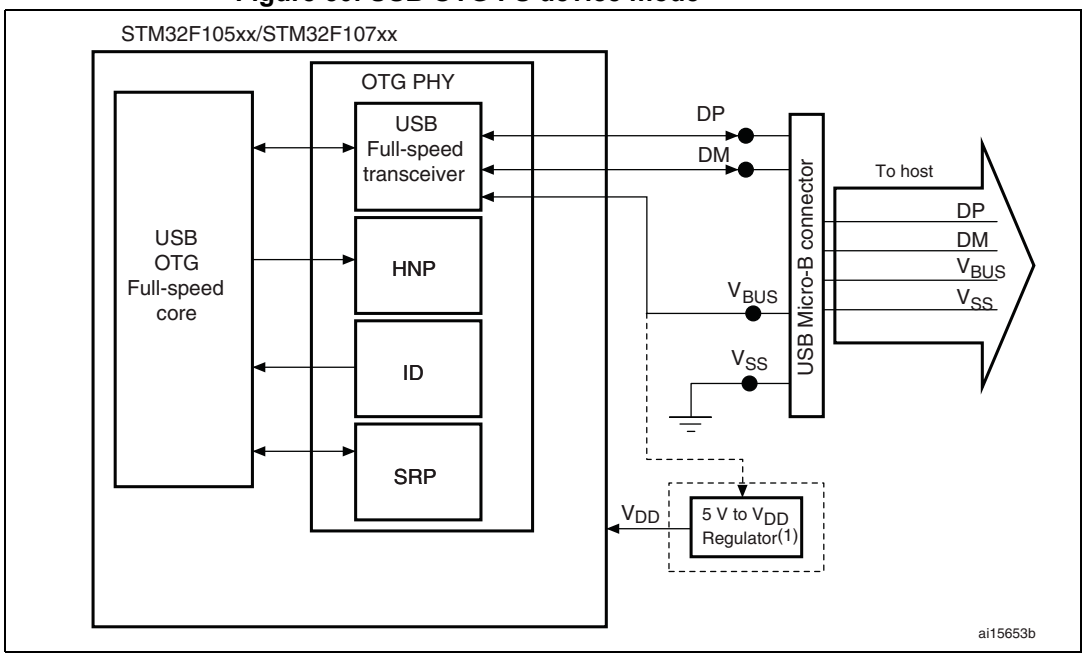
Figure 49. LQFP100 P_D max vs. T_A



Appendix A Application block diagrams

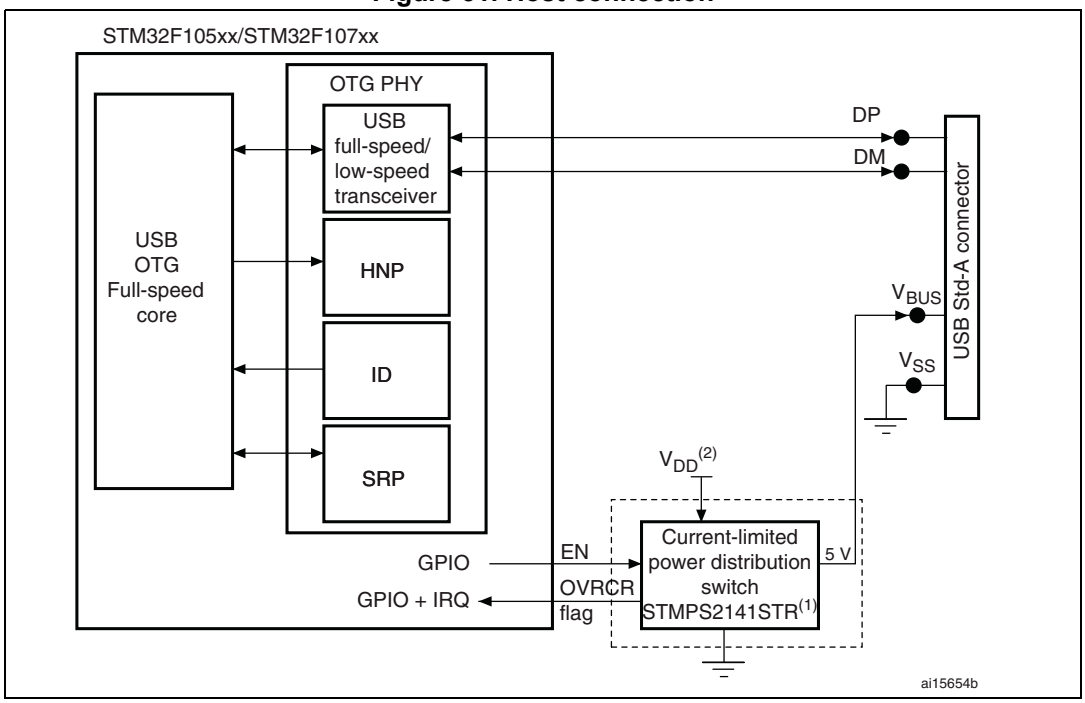
A.1 USB OTG FS interface solutions

Figure 50. USB OTG FS device mode



1. Use a regulator if you want to build a bus-powered device.

Figure 51. Host connection



1. STMPS2141STR needed only if the application has to support bus-powered devices.

8 Revision history

Table 65. Document revision history

Date	Revision	Changes
18-Dec-2008	1	Initial release.
20-Feb-2009	2	I/O information clarified *on page 1. Figure 4: STM32F105xxx and STM32F107xxx connectivity line BGA100 ballout top view* corrected. *Section 2.3.8: Boot modes* updated. PB4, PB13, PB14, PB15, PB3/TRACESWO moved from Default column to Remap column, plus small additional changes in *Table 5: Pin definitions*. Consumption values modified in *Section 5.3.5: Supply current characteristics*. Note modified in *Table 13: Maximum current consumption in Run mode, code with data processing running from Flash* and *Table 15: Maximum current consumption in Sleep mode, code running from Flash or RAM*. *Table 20: High-speed external user clock characteristics* and *Table 21: Low-speed external user clock characteristics* modified. *Table 27: PLL characteristics* modified and *Table 28: PLL2 and PLL3 characteristics* added.